

Paul Berger

List of Publications by Year in descending order

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188
papers

3,096
citations

186265

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214800

47
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193
all docs

193
docs citations

193
times ranked

2754
citing authors

#	ARTICLE	IF	CITATIONS
1	Role of strain and growth conditions on the growth front profile of $\text{In}_x\text{Ga}_{1-x}\text{As}$ on GaAs during the pseudomorphic growth regime. Applied Physics Letters, 1988, 53, 684-686.	3.3	246
2	Plasmon-enhanced optical absorption and photocurrent in organic bulk heterojunction photovoltaic devices using self-assembled layer of silver nanoparticles. Solar Energy Materials and Solar Cells, 2010, 94, 128-132.	6.2	195
3	Room temperature operation of epitaxially grown Si/Si _{0.5} Ge _{0.5} /Si resonant interband tunneling diodes. Applied Physics Letters, 1998, 73, 2191-2193.	3.3	104
4	Polymer solar cells: P3HT:PCBM and beyond. Journal of Renewable and Sustainable Energy, 2018, 10, .	2.0	104
5	Nanometer-period gratings in hydrogen silsesquioxane fabricated by electron beam lithography. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, L12.	1.6	80
6	Full-band simulation of indirect phonon assisted tunneling in a silicon tunnel diode with delta-doped contacts. Applied Physics Letters, 2001, 78, 814-816.	3.3	60
7	Photoresponsivity of polymer thin-film transistors based on polyphenyleneethynylene derivative with improved hole injection. Applied Physics Letters, 2004, 85, 4219-4221.	3.3	60
8	Tri-State Logic Using Vertically Integrated Si ⁺ SiGe Resonant Interband Tunneling Diodes With Double NDR. IEEE Electron Device Letters, 2004, 25, 646-648.	3.9	55
9	Highly repeatable room temperature negative differential resistance in AlN/GaN resonant tunneling diodes grown by molecular beam epitaxy. Applied Physics Letters, 2016, 109, .	3.3	52
10	Low defect densities in molecular beam epitaxial GaAs achieved by isoelectronic In doping. Applied Physics Letters, 1986, 49, 470-472.	3.3	51
11	Current-voltage characteristics of high current density silicon Esaki diodes grown by molecular beam epitaxy and the influence of thermal annealing. IEEE Transactions on Electron Devices, 2000, 47, 1707-1714.	3.0	47
12	4.8% efficient poly(3-hexylthiophene)-fullerene derivative (1:0.8) bulk heterojunction photovoltaic devices with plasma treated AgO _[sub x] /indium tin oxide anode modification. Applied Physics Letters, 2008, 92, 013306.	3.3	47
13	Near-UV electroluminescence in unipolar-doped, bipolar-tunneling GaN/AlN heterostructures. Light: Science and Applications, 2018, 7, 17150-17150.	16.6	47
14	Optical and electronic properties of SiGeC alloys grown on Si substrates. Journal of Crystal Growth, 1995, 157, 386-391.	1.5	45
15	Diffusion barrier cladding in Si/SiGe resonant interband tunneling diodes and their patterned growth on PMOS source/drain regions. IEEE Transactions on Electron Devices, 2003, 50, 1876-1884.	3.0	45
16	Room-temperature negative differential resistance in polymer tunnel diodes using a thin oxide layer and demonstration of threshold logic. Applied Physics Letters, 2005, 87, 203506.	3.3	45
17	Monolithically integrated Si/SiGe resonant interband tunnel diode/CMOS demonstrating low voltage MOBILE operation. Solid-State Electronics, 2004, 48, 1907-1910.	1.4	44
18	In _{0.53} Ga _{0.47} As metal-semiconductor-metal photodiodes with transparent cadmium tin oxide Schottky contacts. Applied Physics Letters, 1994, 65, 1930-1932.	3.3	43

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19	Comparative study of the growth processes of GaAs, AlGaAs, InGaAs, and InAlAs lattice matched and nonlattice matched semiconductors using high-energy electron diffraction. Journal of Applied Physics, 1987, 61, 2856-2860.	2.5	41
20	431 kA/cm ² peak tunneling current density in GaN/AlN resonant tunneling diodes. Applied Physics Letters, 2018, 112, .	3.3	41
21	A study of strain-related effects in the molecular-beam epitaxy growth of In _x Ga _{1-x} As on GaAs using reflection high-energy electron diffraction. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 1162.	1.6	40
22	151 kA/cm ² peak current densities in Si/SiGe resonant interband tunneling diodes for high-power mixed-signal applications. Applied Physics Letters, 2003, 83, 3308-3310.	3.3	38
23	Monolithically Peltier-cooled vertical-cavity surface-emitting lasers. Applied Physics Letters, 1991, 59, 117-119.	3.3	37
24	Transparent and opaque Schottky contacts on undoped In _{0.52} Al _{0.48} As grown by molecular beam epitaxy. Applied Physics Letters, 1995, 66, 3471-3473.	3.3	33
25	Atomic layer deposited HfO ₂ gate dielectrics for low-voltage operating, high-performance poly-(3-hexythiophene) organic thin-film transistors. Organic Electronics, 2010, 11, 1719-1722.	2.6	32
26	Monolithically integrated InP-based front-end photoreceivers. IEEE Transactions on Electron Devices, 1991, 38, 1324-1333.	3.0	31
27	Full band modeling of the excess current in a delta-doped silicon tunnel diode. Journal of Applied Physics, 2003, 94, 5005.	2.5	31
28	Three-terminal Si-based negative differential resistance circuit element with adjustable peak-to-valley current ratios using a monolithic vertical integration. Applied Physics Letters, 2004, 84, 2688-2690.	3.3	31
29	Epitaxially grown Si resonant interband tunnel diodes exhibiting high current densities. IEEE Electron Device Letters, 1999, 20, 329-331.	3.9	30
30	Si resonant interband tunnel diodes grown by low-temperature molecular-beam epitaxy. Applied Physics Letters, 1999, 75, 1308-1310.	3.3	29
31	Demonstration of all-optical modulation in a vertical guided-wave nonlinear coupler. Applied Physics Letters, 1988, 52, 1125-1127.	3.3	28
32	The relation of the performance characteristics of pseudomorphic In _{0.53+x} Ga _{0.47-x} As/In _{0.52} Al _{0.48} As (0 ≤ x ≤ 0.32) modulation-doped field-effect transistors to molecular-beam epitaxial growth modes. Journal of Applied Physics, 1990, 68, 347-350.	2.5	28
33	A waveguide directional coupler with a nonlinear coupling medium. IEEE Journal of Quantum Electronics, 1991, 27, 788-795.	1.9	28
34	Si/SiGe resonant interband tunnel diode with $f_{\text{ro}}/20.2$ GHz and peak current density 218 kA/cm ² for K-band mixed-signal applications. IEEE Electron Device Letters, 2006, 27, 364-367.	3.9	28
35	High 5.2 peak-to-valley current ratio in Si/SiGe resonant interband tunnel diodes grown by chemical vapor deposition. Applied Physics Letters, 2012, 100, .	3.3	28
36	Optical properties of Ge _{1-y} Cy alloys. Journal of Electronic Materials, 1996, 25, 297-300.	2.2	27

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37	Liquid phase epitaxial growth of InGaAs on InP using rare-earth-treated melts. Journal of Applied Physics, 1996, 80, 7094-7103.	2.5	27
38	High electric-field effects on short-channel polythiophene polymer field-effect transistors. Journal of Applied Physics, 2004, 95, 1497-1501.	2.5	27
39	Si/SiGe Resonant Interband Tunneling Diodes Incorporating δ -Doping Layers Grown by Chemical Vapor Deposition. IEEE Electron Device Letters, 2009, 30, 1173-1175.	3.9	27
40	Negative Differential Resistance Devices and Circuits. , 2011, , 176-241.		27
41	MSM photodiodes. IEEE Potentials, 1996, 15, 25-29.	0.3	26
42	The Effect of Spacer Thicknesses on Si-Based Resonant Interband Tunneling Diode Performance and Their Application to Low-Power Tunneling Diode SRAM Circuits. IEEE Transactions on Electron Devices, 2006, 53, 2243-2249.	3.0	26
43	Plasma-Polymerized Multistacked Organic Bipolar Films: A New Approach to Flexible High- κ Dielectrics. Advanced Materials, 2008, 20, 2383-2388.	21.0	26
44	1.3 μ m photoresponsivity in Si-based Ge $_{1-x}$ C $_x$ photodiodes. Applied Physics Letters, 1998, 72, 1860-1862.	3.3	25
45	Investigation of the interface region produced by molecular beam epitaxial regrowth. Journal of Electronic Materials, 1989, 18, 137-142.	2.2	24
46	In _{0.53} Ga _{0.47} As MSM photodiodes with transparent CTO Schottky contacts and digital superlattice grading. IEEE Transactions on Electron Devices, 1997, 44, 2174-2179.	3.0	23
47	Selective deuteron production using target normal sheath acceleration. Physics of Plasmas, 2012, 19, .	1.9	23
48	Superior growth, yield, repeatability, and switching performance in GaN-based resonant tunneling diodes. Applied Physics Letters, 2020, 116, .	3.3	22
49	Band-edge photoluminescence from pseudomorphic Si _{0.96} Sn _{0.04} alloy. Applied Physics Letters, 1996, 68, 3105-3107.	3.3	20
50	Substrate orientation effects on dopant incorporation in InP grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1993, 73, 4095-4097.	2.5	19
51	Performance characteristics of GaInAs/GaAs large optical cavity quantum well lasers. Electronics Letters, 1991, 27, 680.	1.0	18
52	Annealing of defect density and excess currents in Si-based tunnel diodes grown by low-temperature molecular-beam epitaxy. Journal of Applied Physics, 2004, 96, 747-753.	2.5	17
53	Capacitance-voltage characterization of pulsed plasma polymerized allylamine dielectrics for flexible polymeric field effect transistors. Journal of Electronic Materials, 2004, 33, 1240-1247.	2.2	17
54	RF Performance and Modeling of Si/SiGe Resonant Interband Tunneling Diodes. IEEE Transactions on Electron Devices, 2005, 52, 2129-2135.	3.0	17

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55	930 kA/cm ² peak tunneling current density in GaN/AlN resonant tunneling diodes grown on MOCVD GaN-on-sapphire template. Applied Physics Letters, 2019, 114, .	3.3	17
56	Epitaxial Si-based tunnel diodes. Thin Solid Films, 2000, 380, 145-150.	1.8	16
57	Growth temperature and dopant species effects on deep levels in Si grown by low temperature molecular beam epitaxy. Journal of Applied Physics, 2003, 93, 9104-9110.	2.5	16
58	90 nm 32 \times 32 bit Tunneling SRAM Memory Array With 0.5 ns Write Access Time, 1 ns Read Access Time and 0.5 V Operation. IEEE Transactions on Circuits and Systems I: Regular Papers, 2011, 58, 2432-2445.	5.4	16
59	Orientation-dependent phase modulation in InGaAs/GaAs multiquantum well waveguides. Applied Physics Letters, 1988, 53, 2129-2131.	3.3	15
60	α -Si interband tunnel diode grown by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 290.	1.6	15
61	High sensitivity Si-based backward diodes for zero-biased square-law detection and the effect of post-growth annealing on performance. IEEE Electron Device Letters, 2005, 26, 575-578.	3.9	15
62	Characterization and Electrical Properties of Individual Au-NiO-Au Heterojunction Nanowires. IEEE Nanotechnology Magazine, 2007, 6, 676-681.	2.0	15
63	Plasma-polymerized multistacked bipolar gate dielectric for organic thin-film transistors. Organic Electronics, 2010, 11, 1767-1771.	2.6	15
64	Viability Bounds of M2M Communication Using Energy-Harvesting and Passive Wake-Up Radio. IEEE Access, 2017, 5, 27868-27878.	4.2	15
65	Flexible, solution-processed, indium oxide (In ₂ O ₃) thin film transistors (TFT) and circuits for internet-of-things (IoT). Materials Science in Semiconductor Processing, 2022, 139, 106354.	4.0	15
66	Realization of in-situ sub two-dimensional quantum structures by strained layer growth phenomena in the In _x Ga _{1-x} As/GaAs system. Journal of Electronic Materials, 1996, 25, 479-483.	2.2	14
67	Metal-semiconductor-metal photodetectors. , 2001, 4285, 198.		14
68	Printed and organic diodes: devices, circuits and applications. Flexible and Printed Electronics, 2017, 2, 033001.	2.7	14
69	Investigation of molecular beam epitaxial In _{0.53} Ga _{0.47} As regrown on liquid phase epitaxial In _{0.53} Ga _{0.47} As/InP. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 540.	1.6	13
70	InGaAs/GaAs multiquantum-well electroabsorption modulator with integrated waveguide. Optics Letters, 1987, 12, 820.	3.3	13
71	Growth and properties of In _{0.52} Al _{0.48} As/In _{0.53} Ga _{0.47} As, GaAs: In and InGaAs/GaAs multilayers. Journal of Crystal Growth, 1987, 81, 373-377.	1.5	13
72	10 GHz bandwidth monolithic α -Si modulated doped field effect transistor photoreceiver. Applied Physics Letters, 1993, 63, 2115-2116.	3.3	13

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73	Fabrication of nanowires with high aspect ratios utilized by dry etching with SF ₆ :C ₄ F ₈ and self-limiting thermal oxidation on Si substrate. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, 763-768.	1.2	13
74	0.6V Threshold Voltage Thin Film Transistors With Solution Processable Indium Oxide (In ₂ O ₃) Channel and Anodized High- κ Al ₂ O ₃ Dielectric. IEEE Electron Device Letters, 2019, 40, 1112-1115.	3.9	13
75	GaAs quantum well laser and heterojunction bipolar transistor integration using molecular beam epitaxial regrowth. Applied Physics Letters, 1991, 59, 2826-2828.	3.3	12
76	Strain modification in thin Si _{1-x} Ge _x alloys on (100) Si for formation of high density and uniformly sized quantum dots. Journal of Applied Physics, 1999, 85, 578-582.	2.5	12
77	Sensitivity of Si-based zero-bias backward diodes for microwave detection. Electronics Letters, 2007, 43, 295.	1.0	12
78	Anodic Oxidation of Ultra-Thin Ti Layers on ITO Substrates and their Application in Organic Electronic Memory Elements. Electrochimica Acta, 2014, 137, 91-98.	5.2	12
79	Investigation of Switching Time in GaN/AlN Resonant Tunneling Diodes by Experiments and P-SPICE Models. IEEE Transactions on Electron Devices, 2020, 67, 75-79.	3.0	12
80	Substantial improvement by substrate misorientation in dc performance of Al _{0.5} Ga _{0.5} As/GaAs/Al _{0.5} Ga _{0.5} As double-heterojunction NPN bipolar transistors grown by molecular beam epitaxy. Applied Physics Letters, 1991, 59, 186-188.	3.3	11
81	Integration of Si/SiGe HBT and Si-based RITD demonstrating controllable negative differential resistance for wireless applications. Solid-State Electronics, 2006, 50, 973-978.	1.4	11
82	Boron Delta-Doping Dependence on Si/SiGe Resonant Interband Tunneling Diodes Grown by Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2012, 59, 602-609.	3.0	11
83	AlN/GaN/AlN resonant tunneling diodes grown by rf-plasma assisted molecular beam epitaxy on freestanding GaN. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	1.2	11
84	In _{0.53} Ga _{0.47} As p-n photodiodes with transparent cadmium tin oxide contacts. Applied Physics Letters, 1992, 61, 1673-1675.	3.3	10
85	Current transport characteristics of SiGeC/Si heterojunction diode. IEEE Electron Device Letters, 1996, 17, 589-591.	3.9	10
86	P and B doped Si resonant interband tunnel diodes with as-grown negative differential resistance. Electronics Letters, 2009, 45, 759.	1.0	10
87	Feasibility and Fundamental Limits of Energy-Harvesting Based M2M Communications. International Journal of Wireless Information Networks, 2017, 24, 291-299.	2.7	10
88	1.0 GHz monolithic p-i-n MODFET photoreceiver using molecular beam epitaxial regrowth. IEEE Photonics Technology Letters, 1992, 4, 891-894.	2.5	9
89	pnp Si resonant interband tunnel diode with symmetrical NDR. Electronics Letters, 2001, 37, 1412.	1.0	9
90	Radiation tolerance of Si/Si _{0.6} Ge _{0.4} resonant interband tunneling diodes. Journal of Applied Physics, 2004, 95, 6406-6408.	2.5	9

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91	NMOS/SiGe Resonant Interband Tunneling Diode Static Random Access Memory. , 2006, , .		9
92	Interfacial design and structure of protein/polymer films on oxidized AlGaIn surfaces. Journal Physics D: Applied Physics, 2011, 44, 034010.	2.8	9
93	A Nonlinear Circuit Simulation of Switching Process in Resonant-Tunneling Diodes. IEEE Transactions on Electron Devices, 2016, 63, 4993-4997.	3.0	9
94	Molecular beam epitaxial growth and luminescence of In _x Ga _{1-x} As/In _x Al _{1-x} As multiquantum wells on GaAs. Applied Physics Letters, 1987, 51, 261-263.	3.3	8
95	Anomalous effects of lamp annealing in modulation-doped In _{0.53} Ga _{0.47} As/In _{0.52} Al _{0.48} As and Si-implanted In _{0.53} Ga _{0.47} As. IEEE Transactions on Electron Devices, 1987, 34, 235-240.	3.0	8
96	Analysis of the Voltage Swing for Logic and Memory Applications in Si/SiGe Resonant Interband Tunnel Diodes Grown by Molecular Beam Epitaxy. IEEE Nanotechnology Magazine, 2007, 6, 158-163.	2.0	8
97	0.7-GHz Solution-Processed Indium Oxide Rectifying Diodes. IEEE Transactions on Electron Devices, 2020, 67, 360-364.	3.0	8
98	An AlGaAs double-heterojunction bipolar transistor grown by molecular-beam epitaxy. Applied Physics Letters, 1991, 59, 1099-1101.	3.3	7
99	8-element linear array monolithic p-i-n MODFET photoreceivers using molecular beam epitaxial regrowth. IEEE Photonics Technology Letters, 1993, 5, 63-66.	2.5	7
100	Si-based interband tunneling devices for high-speed logic and low power memory applications. , 0, , .		7
101	Strain-Engineered Si/SiGe Resonant Interband Tunneling Diodes Grown on $\text{Si}_{0.8}\text{Ge}_{0.2}$ Virtual Substrates With Strained Si Cladding Layers. IEEE Electron Device Letters, 2008, 29, 599-602.	3.9	7
102	Experimental determination of quantum-well lifetime effect on large-signal resonant tunneling diode switching time. Applied Physics Letters, 2015, 107, .	3.3	7
103	Negative differential resistance in polymer tunnel diodes using atomic layer deposited, TiO ₂ tunneling barriers at various deposition temperatures. Organic Electronics, 2017, 47, 228-234.	2.6	7
104	Effects of growth temperature on electrical properties of GaN/AlN based resonant tunneling diodes with peak current density up to 1.01 MA/cm ² . AIP Advances, 2020, 10, .	1.3	7
105	Recombination velocity at molecular-beam-epitaxial GaAs regrown interfaces. Journal of Applied Physics, 1989, 65, 2571-2573.	2.5	6
106	Monolithically integrated Si/SiGe resonant interband tunneling diodes/CMOS mobile latch with high voltage swing. , 0, , .		6
107	Improved vertically stacked Si ⁺ -SiGe resonant interband tunnel diode pair with small peak voltage shift and unequal peak currents. Electronics Letters, 2004, 40, 1548.	1.0	6
108	Low sidewall damage plasma etching using ICP-RIE with HBr chemistry of Si ⁺ -SiGe resonant interband tunnel diodes. Electronics Letters, 2006, 42, 719.	1.0	6

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109	Pulsed plasma polymerized dichlorotetramethylsiloxane high-k gate dielectrics for polymer field-effect transistors. Journal of Applied Physics, 2006, 99, 014104.	2.5	6
110	Towards <i>in vivo</i> biosensors for low-cost protein sensing. Electronics Letters, 2013, 49, 450-451.	1.0	6
111	Feasibility and fundamental limits of energy-harvesting based M2M communications. , 2016, , .		6
112	Selective atomic layer deposition on flexible polymeric substrates employing a polyimide adhesive as a physical mask. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 012405.	2.1	6
113	Monolithic integration of GaAs and In _{0.2} Ga _{0.8} As lasers by molecular beam epitaxy on GaAs. Applied Physics Letters, 1991, 58, 2698-2700.	3.3	5
114	A p-Ge/ _{1-x} C/ _x /n-Si heterojunction diode grown by molecular beam epitaxy. IEEE Electron Device Letters, 1997, 18, 411-413.	3.9	5
115	Overgrown Si/SiGe resonant interband tunnel diodes for integration with CMOS. , 0, , .		5
116	Enhanced Emission Using Thin Li-Halide Cathodic Interlayers for Improved Injection into Poly(p-phenylene vinylene) Derivative PLEDs. Electrochemical and Solid-State Letters, 2008, 11, J76.	2.2	5
117	Methods for attaining high interband tunneling current in III-Nitrides. , 2012, , .		5
118	Tuning the Plasmonic Extinction Resonances of Hexagonal Arrays of Ag Nanoparticles. Plasmonics, 2015, 10, 1505-1512.	3.4	5
119	M2M Communication Assessment in Energy-Harvesting and Wake-Up Radio Assisted Scenarios Using Practical Components. Sensors, 2018, 18, 3992.	3.8	5
120	Growth phenomena and characteristics of strained In _x Ga _{1-x} As on GaAs. Journal of Crystal Growth, 1989, 95, 193-196.	1.5	4
121	Low resistance ohmic contacts to p-Ge/ _{1-x} C/ _x on Si. IEEE Electron Device Letters, 1997, 18, 7-9.	3.9	4
122	Antireflection coatings based on fluoride formulations for organic solar cells. Technical Physics Letters, 2016, 42, 359-361.	0.7	4
123	Antireflection composite coatings for organic solar cells. Applied Solar Energy (English Translation) Tj ETQq1 1 0.784314 rgBT ₄ /Overlock	1.6	4
124	Advancements in Solution Processable Devices using Metal Oxides For Printed Internet-of-Things Objects. , 2019, , .		4
125	Dependence of growth temperature on the electrical properties and microstructure of MBE-grown AlN/GaN resonant tunneling diodes on sapphire. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2020, 38, 032214.	1.2	4
126	Electroluminescence in Unipolar-Doped Resonant-Tunneling Diodes: A Competition between Interband Tunneling and Impact Ionization. Physical Review Applied, 2021, 16, .	1.8	4

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127	Monolithic GaAs/AlGaAs pin MESFET photoreceiver using a single molecular beam epitaxy growth step. Electronics Letters, 1993, 29, 1133.	1.0	3
128	Challenges in integration of Resonant Interband Tunnel Devices with CMOS. , 0, , .		3
129	Strain engineered Si ^{1-x} SiGe resonant interband tunneling diodes with outside barriers grown on Si _{0.8} Ge _{0.2} virtual substrates. Applied Physics Letters, 2008, 93, 102113.	3.3	3
130	Observation of strain in pseudomorphic Si ^{1-x} Ge _x by tracking phonon participation in Si ^{1-x} SiGe resonant interband tunnel diodes via electron tunneling spectroscopy. Journal of Applied Physics, 2009, 106, 034501.	2.5	3
131	Wireless Energy Harvesting and Communications: Limits and Reliability. , 2017, , .		3
132	Increasing the Efficiency of Organic Solar Cells by Antireflection Coatings Based on Fluoride Composites. Technical Physics Letters, 2018, 44, 295-296.	0.7	3
133	Monolithic GaAs/AlGaAs optical transmitter circuit using a single growth step. Electronics Letters, 1994, 30, 490-491.	1.0	3
134	<title>Buried heterostucture lasers using a single-step metal-organic chemical vapor deposition growth over patterned substrates</title>. , 1992, 1676, 117.		2
135	Inverted, substrate-removed MSM and Schottky diode optical detectors. , 0, , .		2
136	Near band edge photoluminescence from pseudomorphic tensially strained Si _{0.985} Co _{0.015} alloy. Thin Solid Films, 1997, 294, 122-124.	1.8	2
137	Temperature dependent DC ^{RF} performance of Si ^{1-x} SiGe resonant interband tunnelling diodes. Electronics Letters, 2005, 41, 559.	1.0	2
138	High-k Polymerized Dichlorotetramethyldisiloxane Films Deposited by Radio Frequency Pulsed Plasma for Gate Dielectrics in Polymer Field Effect Transistors. Materials Research Society Symposia Proceedings, 2005, 870, 131.	0.1	2
139	Delta-Doped Si/SiGe Zero-Bias Backward Diodes for Micro-Wave Detection. Device Research Conference, IEEE Annual, 2007, , .	0.0	2
140	Broadband Finite ^{Time} Difference Time ^{Domain} Modeling of Plasmonic Organic Photovoltaics. ETRI Journal, 2014, 36, 654-661.	2.0	2
141	2-volt Solution-Processed, Indium Oxide (In ₂ O ₃) Thin Film Transistors on flexible Kapton. , 2019, , .		2
142	RTD Light Emission around 1550 nm with IQE up to 6% at 300 K. , 2020, , .		2
143	Flexible, Gallium Oxide (Ga ₂ O ₃) Thin Film Transistors (TFTs) and Circuits for the Internet of Things (IoT). , 2021, , .		2
144	Long Wavelength Metal-semiconductor-metal Photodiodes With Transparent Cadmium Tin Oxide Schottky Contacts. , 0, , .		1

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145	<title>Equivalent circuit modeling of metal-semiconductor-metal photodiodes with transparent conductor electrodes</title>. , 1997, , .		1
146	Photoluminescence Of Sisnc Alloys Grown On (100) Si Substrates. Materials Research Society Symposia Proceedings, 1998, 533, 327.	0.1	1
147	Development of $\hat{B}/i\text{-Si}/\hat{Sb}$ and $\hat{B}/i\text{-Si}/\hat{Sb}/i\text{-Si}/\hat{B}$ resonant interband tunnel diodes for integrated circuit applications. , 0, , .		1
148	SiGe diffusion barriers for P-doped Si/SiGe resonant interband tunnel diodes. , 0, , .		1
149	Monolithic vertical integration of Si/SiGe HBT and Si-based resonant interband tunneling diode demonstrating latching operation and adjustable peak-to-valley current ratios. , 0, , .		1
150	Analysis of the Biasing Conditions and Latching Operation for Si/SiGe Resonant Interband Tunnel Diode Based Tunneling SRAM. , 0, , .		1
151	High Temperature Characterization of Si/SiGe Resonant Interband Tunnel Diodes. , 0, , .		1
152	Simplified Si resonant interband tunnel diodes. , 2007, , .		1
153	New Device Physics of Cross-Gap Electroluminescence in Unipolar-Doped InGaAs/AlAs RTDs. , 2019, , .		1
154	In-Situ RHEED Studies To Understand The Dislocation Formation Process In Growth Of InGaAs on GaAs. , 1988, 0944, 10.		0
155	Effects of substrate tilting in substantial improvement of DC performance of AlGaAs/GaAs n-p-n DHBTs grown by MBE. IEEE Transactions on Electron Devices, 1991, 38, 2717-2718.	3.0	0
156	Integrated photoreceiver array using molecular beam epitaxial regrowth. , 0, , .		0
157	Monolithic PIN-FET photoreceivers. , 0, , .		0
158	<title>Monolithic p-i-n-FET photoreceivers</title>. , 1994, 2149, 414.		0
159	Liquid phase epitaxial InGaAs on InP with rare-earth elements. , 0, , .		0
160	Liquid-phase epitaxial growth process of InGaAs on InP with rare-earth treatment. , 1996, , .		0
161	Ge $1-x$ C x /Si heterojunction photodiode. , 1997, 3007, 162.		0
162	Electrical and optical properties of phosphorus doped Ge $1\hat{a}^3y$ Cy. Thin Solid Films, 1998, 321, 47-50.	1.8	0

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163	<title>Optically interconnected static RAM for instruction-level parallel processors</title> . , 1999, , .		0
164	Integration of silicon-based tunnel diodes with CMOS: an RIT-OSU-NRL-NSF effort. , 0, , .		0
165	Capacitance-Voltage Characterization of Pulsed Plasma Polymerized Allylamine Dielectrics. Materials Research Society Symposia Proceedings, 2002, 736, 1.	0.1	0
166	Growth Temperature Effects on Deep-Levels in Si Grown by Low Temperature Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2002, 745, 691.	0.1	0
167	Light Sensitive Polymer Thin Film Transistors Based on BAS-PPE. Materials Research Society Symposia Proceedings, 2004, 814, 152.	0.1	0
168	A combined model for Si-based resonant interband tunneling diodes grown on SOI. , 0, , .		0
169	Phosphorus diffusion in Si-based resonant interband tunneling diodes and tri-state logic using vertically stacked diodes. Materials Science in Semiconductor Processing, 2005, 8, 411-416.	4.0	0
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